TPA6133A2 138mW DirectPath™ 立体声耳机放大器

1 特性

- DirectPath™ 接地基准输出
  - 免除了对输出直流 (DC) 阻断电容器的需要
  - 减少了电路板面积
  - 减少了组件高度和成本
  - 无衰减的全低音响应
- 电源电压范围：2.5V 至 5.5V
- 高电源抑制比 (> 100dB PSRR)
- 针对最大噪声抑制的差分输入（69dB 共模抑制比 (CMRR)）
- 禁用后保持高阻抗输出
- 高级爆音/喀嗒噪声抑制电路
- 针对关断的通用输入输出 (GPIO) 控制
- 20 引脚，4mm x 4mm 超薄四方扁平无引线 (WQFN) 封装

2 应用范围

- 移动电话
- 音频耳机
- 笔记本电脑
- 高保真应用

3 说明

TPA6133A2是一款具有 GPIO 控制的立体声 DirectPath™ 头戴式耳机放大器。 TPA6133A2具有最小的静态流耗，I_{DD}的典型值为 4.2mA，这使得它非常适合于便携式应用。 GPIO 控制使得此器件能够被置于低功耗关断模式中。

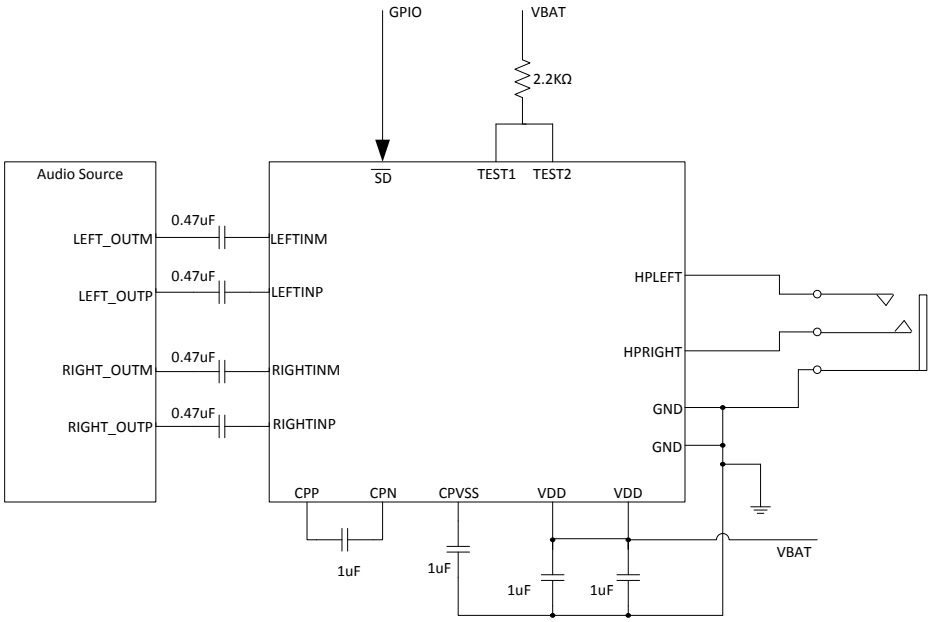
TPA6133A2是一款信噪比为 93dB 的高保真放大器。大于 100dB 的 PSRR 可在不影响收听体验的同时实现与电池的直接连接。 12 μVrms 的输出噪声（典型值*输入信噪比 (A-weighted)*）在默声周期期间提供最小的噪声背景。 可配置差分输入和高 CMRR 可在一个移动器件所处的嘈杂环境中实现最大噪声抑制。

器件信息(1)

部件号	封装	封装尺寸（标称值）
TPA6133A2	超薄四方扁平无引线 (WQFN) (20)	4.00mm x 4.00mm

(1) 如需了解所有可用封装，请见数据表末尾的可订购产品附录。

4 简化应用示意图



PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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5 修订历史记录

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (August 2014) to Revision B	Page
• Changed "PIN QFN" To: "NUMBER" in the Pin Functions table	3
• Added a NOTE to the Applications and Implementation section	13
• Added new paragraph to the Application Information section	13

Changes from Original (June 2013) to Revision A	Page
• 添加了处理额定值表，特性描述部分，器件功能模式，应用和实施部分，电源相关建议部分，布局部分，器件和文档支持部分以及机械、封装和可订购信息部分。	1
• 添加了器件信息表	1
• Moved "Minimum Load Impedance" From the Absolute Maximum Ratings table To the Recommended Operating Conditions table	4
• Added the Thermal Information Table	4
• Changed text in the Overview section From: "toggling the $\overline{SD}$ pin to logic 1." To: "asserting the $\overline{SD}$ pin to logic 1."	10
• Changed text in the Headphone Amplifier section From: "the output signal is severely clipped" To: "power consumption will be higher"	11
• Added the Optional Test Setup section	15
• Added the Layout Example image	17

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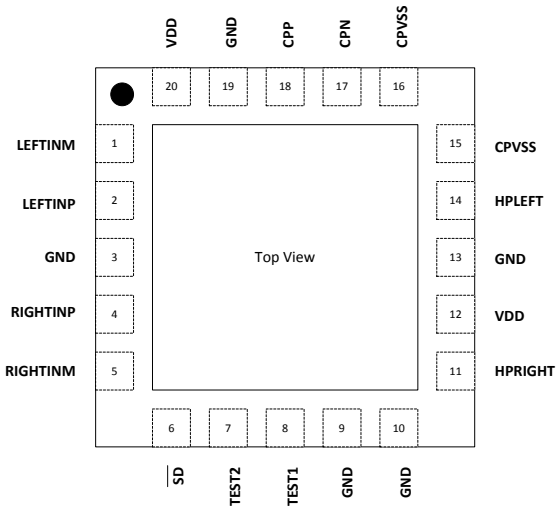
6 Pin Configuration and Functions

RTJ Package
(Top VIEW)



Pin Functions

PIN		INPUT, OUTPUT, POWER	DESCRIPTION
NAME	NUMBER		
LEFTINM	1	I	Left channel negative differential input. Impedance must be matched to LEFTINP. Connect the left input to LEFTINM when using single-ended inputs.
LEFTINP	2	I	Left channel positive differential input. Impedance must be matched to LEFTINM. AC ground LEFTINP near signal source while maintaining matched impedance to LEFTINM when using single-ended inputs.
RIGHTINP	4	I	Right channel positive differential input. Impedance must be matched to RIGHTINM. AC ground RIGHTINP near signal source while maintaining matched impedance to RIGHTINM when using single-ended inputs.
GND	3, 9, 10, 13	P	Analog ground. Must be connected to common supply GND. It is recommended that this pin be used to decouple V_{DD} for analog. Use pin 13 to decouple pin 12 on the QFN package.
RIGHTINM	5	I	Right channel negative differential input. Impedance must be matched to RIGHTINP. Connect the right input to RIGHTINM when using single-ended inputs.
$\overline{SD}$	6	I	Shutdown. Active low logic. 5V tolerant input.
TEST2	7	I	Factory test pins. Pull up to VDD supply. See Applications Diagram.
TEST1	8	I	Factory test pins. Pull up to VDD supply. See Applications Diagram.
HPRIGHT	11	O	Headphone light channel output. Connect to the right terminal of the headphone jack.
V_{DD}	12	P	Analog V_{DD}. V_{DD} must be connected to common V_{DD} supply. Decouple with its own 1-µF capacitor to analog ground (pin 13).
HPLEFT	14	O	Headphone left channel output. Connect to left terminal of headphone jack.
CPVSS	15, 16	P	Negative supply generated by the charge pump. Decouple to pin 19 or a GND plane. Use a 1 µF capacitor.
CPN	17	P	Charge pump flying capacitor negative terminal. Connect one side of the flying capacitor to CPN.
CPP	18	P	Charge pump flying capacitor positive terminal. Connect one side of the flying capacitor to CPP.
GND	19	P	Charge pump ground. GND must be connected to common supply GND. It is recommended that this pin be decoupled to the V_{DD} of the charge pump pin (pin 20 on the QFN).
V_{DD}	20	P	Charge pump voltage supply. V_{DD} must be connected to the common V_{DD} voltage supply. Decouple to GND (pin 19) with its own 1 µF capacitor.
Thermal pad	Die Pad	P	Solder the thermal pad on the bottom of the QFN package to the GND plane of the PCB. It is required for mechanical stability and will enhance thermal performance.

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7 Specification

7.1 Absolute Maximum Ratings[(1)]

over operating free-air temperature range, T_A = 25°C (unless otherwise noted)

		MIN	MAX	UNIT
Supply voltage, V_{DD}		–0.3	6	V
Input voltage	RIGHTINx, LEFTINx	CPVSS-0.2 V to minimum of (3.6 V, VDD+0.2 V)		
	$\overline{SD}$, TEST1, TEST2	–0.3	7	V
Output continuous total power dissipation		See the Thermal Information Table		
Operating free-air temperature range, T_A		–40	85	°C
Operating junction temperature range, T_J		–40	150	°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 Handling Ratings

			MIN	MAX	UNIT
T_{stg}	Storage temperature range		–65	150	°C
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins[(1)]	–3	3	kV
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins[(2)]	–750	750	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

			MIN	MAX	UNIT
	Supply voltage, V_{DD}		2.5	5.5	V
V_{IH}	High-level input voltage	TEST1, TEST2, $\overline{SD}$	1.3		V
V_{IL}	Low-level input voltage	$\overline{SD}$		0.35	V
	Minimum Load Impedance		12.8		Ω
T_A	Operating free-air temperature		–40	85	°C

7.4 Thermal Information

THERMAL METRIC[(1)]		RTJ 20 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	34.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	32.5	
$R_{\theta JB}$	Junction-to-board thermal resistance	11.6	
ψ_{JT}	Junction-to-top characterization parameter	0.4	
ψ_{JB}	Junction-to-board characterization parameter	11.6	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	3.1	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

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7.5 Electrical Characteristics

T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$\|V_{OS}\|$	Output offset voltage	V_{DD} = 2.5 V to 5.5 V, inputs grounded			135	400	µV
PSRR	DC Power supply rejection ratio	V_{DD} = 2.5 V to 5.5 V, inputs grounded			–101	-85	dB
CMRR	Common mode rejection ratio	V_{DD} = 2.5 V to 5.5 V			–69		dB
$\|I_{IH}\|$	High-level input current	V_{DD} = 5.5 V, V_I = V_{DD}	TEST1, TEST2			1	µA
			$\overline{SD}$			10	
$\|I_{IL}\|$	Low-level input current	V_{DD} = 5.5 V, V_I = 0 V	$\overline{SD}$			1	µA
I_{DD}	Supply current	V_{DD} = 2.5 V to 5.5 V, $\overline{SD}$ = V_{DD}			4.2	6	mA
		Shutdown mode, V_{DD} = 2.5V to 5.5 V, $\overline{SD}$ = 0 V			0.08	1	µA

7.6 Operating Characteristics

V_{DD} = 3.6 V , T_A = 25°C, R_L = 16 Ω (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
P_O	Output power	Stereo, Outputs out of phase, THD = 1%, f = 1 kHz, Gain = +4 dB	V_{DD} = 2.5V		63		mW
			V_{DD} = 3.6V		133		
			V_{DD} = 5V		142		
THD+N	Total harmonic distortion plus noise	P_O = 35 mW	f = 100 Hz		0.0096%		
			f = 1 kHz		0.007%		
			f = 20 kHz		0.0021%		
k_{SVR}	Supply ripple rejection ratio	200 mV_{pp} ripple, f = 217 Hz			-94.3	-85	dB
		200 mV_{pp} ripple, f = 1 kHz			-92		
		200 mV_{pp} ripple, f = 20 kHz			-77.1		
A_v	Channel DC Gain	$\overline{SD}$ = V_{DD}			1.597		V/V
ΔA_v	Gain matching				0.1%		
	Slew rate				0.4		V/µs
V_n	Noise output voltage	V_{DD} = 3.6V, A-weighted, Gain = +4 dB			12		$µV_{RMS}$
f_{osc}	Charge pump switching frequency			300	381	500	kHz
	Start-up time from shutdown				4.8		ms
	Differential input impedance				36.6		kΩ
SNR	Signal-to-noise ratio	P_o = 35 mW			93		dB
	Thermal shutdown	Threshold			180		°C
		Hysteresis			35		°C
Z_O	HW Shutdown HP output impedance	$\overline{SD}$ = 0 V, measured output to ground.			112		Ω
C_O	Output capacitance				80		pF

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7.7 Typical Characteristics

Table 1. Table of Graphs

		Figure
Total harmonic distortion + noise	versus Output power	Figure 1–Figure 4
Total harmonic distortion + noise	versus Frequency	Figure 5–Figure 12
Supply voltage rejection ratio	versus Frequency	Figure 13-Figure 14
Common mode rejection ratio	versus Frequency	Figure 15-Figure 16
Crosstalk	versus Frequency	Figure 17-Figure 18

$C_{(PUMP,\ DECOUPLE,\ ,BYPASS,\ CPVSS)}$ = 1 µF, C_I = 2.2 µF.
All THD + N graphs taken with outputs out of phase (unless otherwise noted).

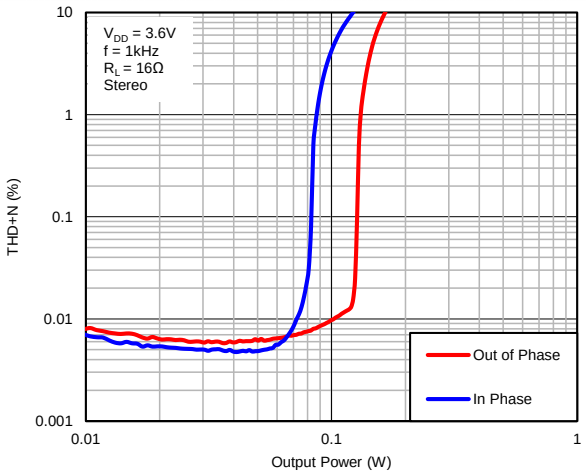

Figure 1. Total Harmonic Distortion + Noise vs Output Power

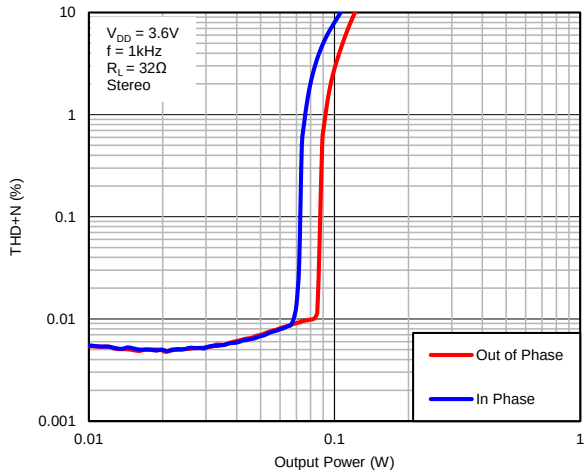

Figure 2. Total Harmonic Distortion + Noise vs Output Power

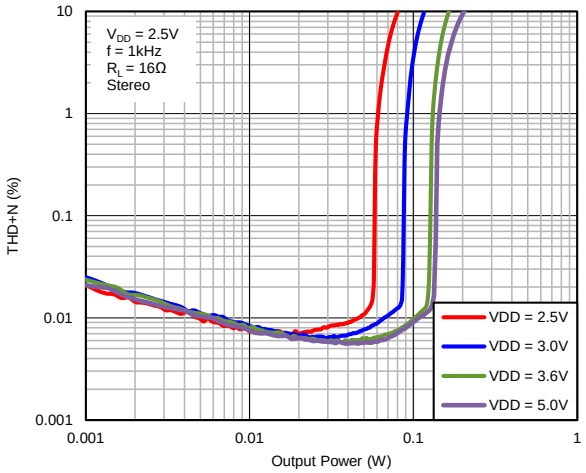

Figure 3. Total Harmonic Distortion + Noise vs Output Power

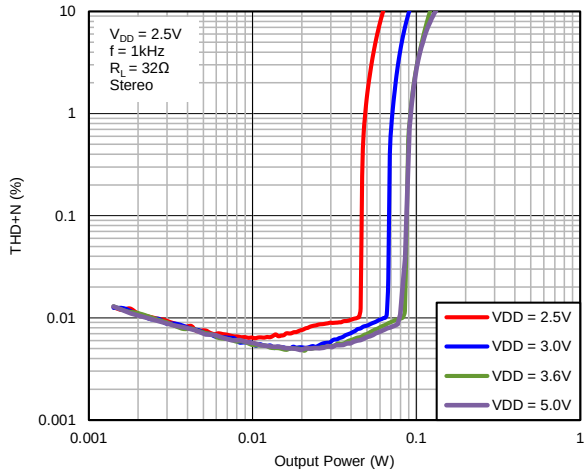

Figure 4. Total Harmonic Distortion + Noise vs Output Power

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All THD + N graphs taken with outputs out of phase (unless otherwise noted).

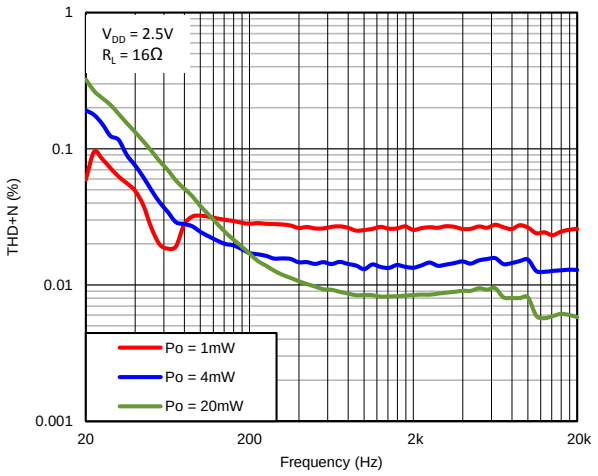

Figure 5. Total Harmonic Distortion + Noise vs Frequency

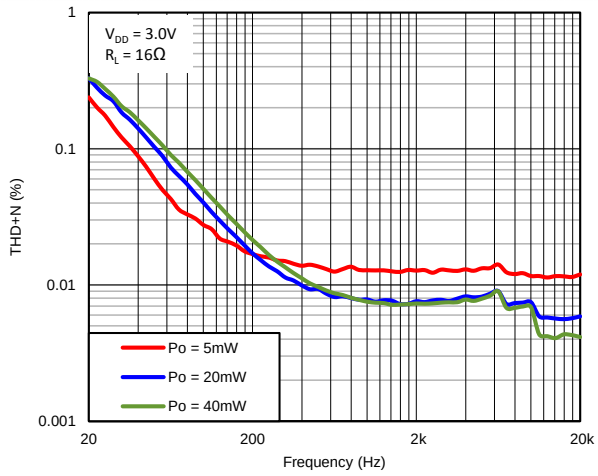

Figure 6. Total Harmonic Distortion + Noise vs Frequency

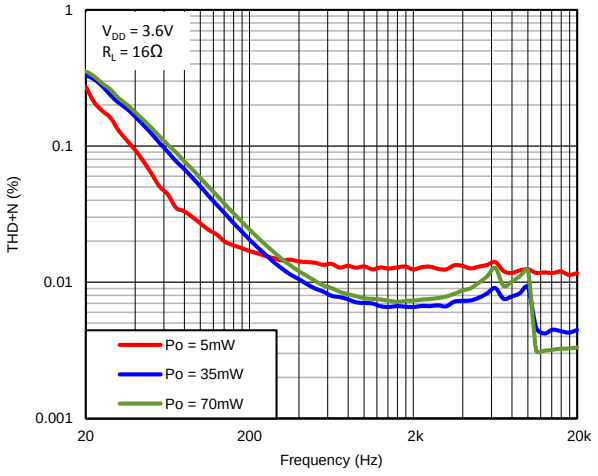

Figure 7. Total Harmonic Distortion + Noise vs Frequency

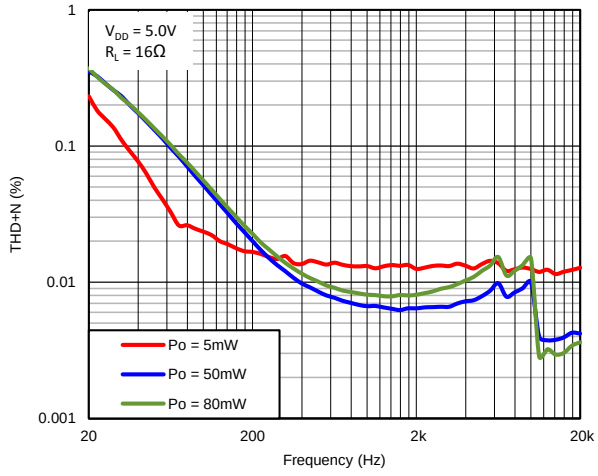

Figure 8. Total Harmonic Distortion + Noise vs Frequency

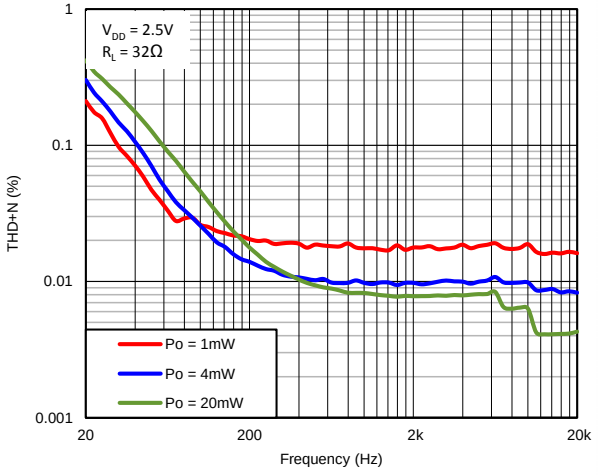

Figure 9. Total Harmonic Distortion + Noise vs Frequency

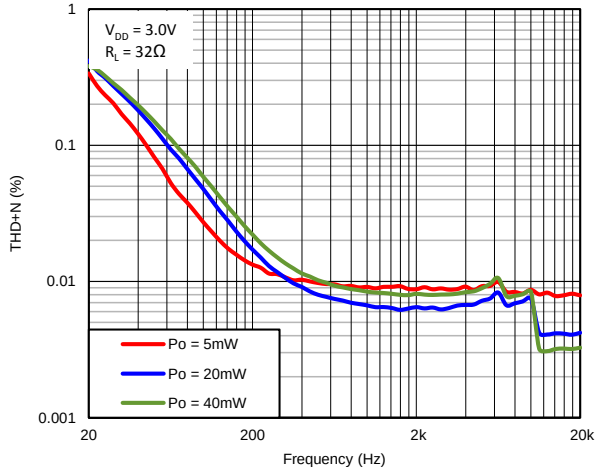

Figure 10. Total Harmonic Distortion + Noise vs Frequency

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All THD + N graphs taken with outputs out of phase (unless otherwise noted).

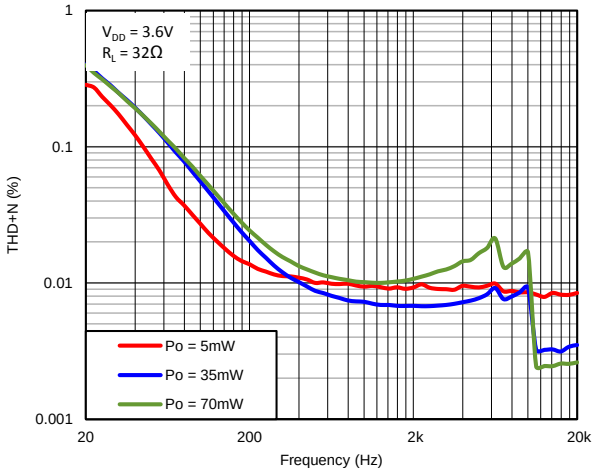

Figure 11. Total Harmonic Distortion + Noise vs Frequency

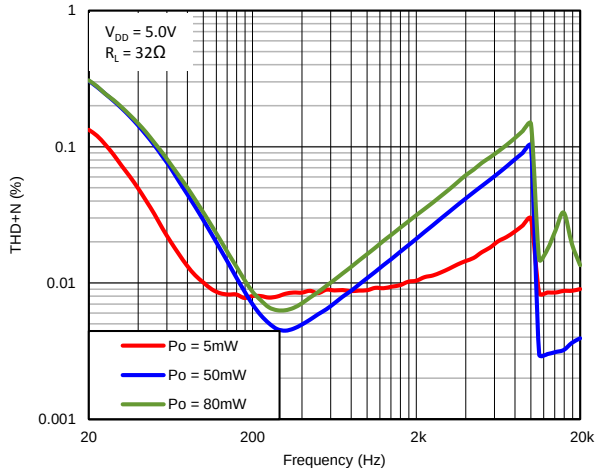

Figure 12. Total Harmonic Distortion + Noise vs Frequency

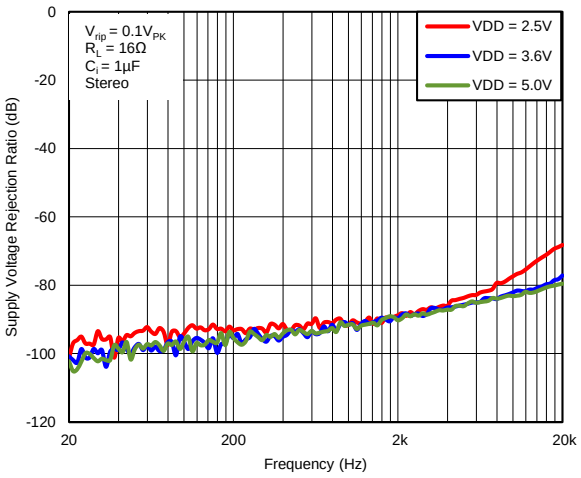

Figure 13. Supply Voltage Rejection Ratio vs Frequency

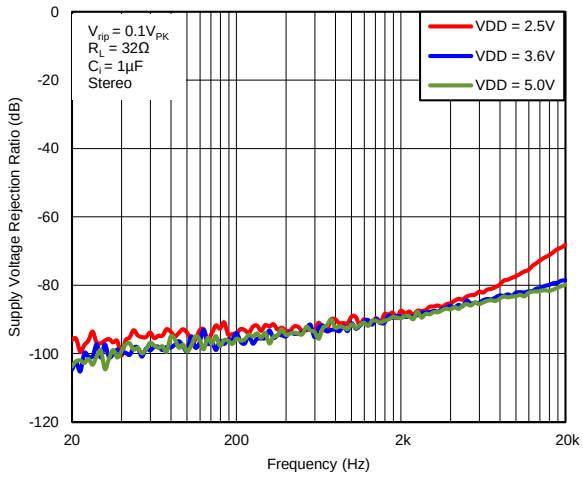

Figure 14. Supply Voltage Rejection Ratio vs Frequency

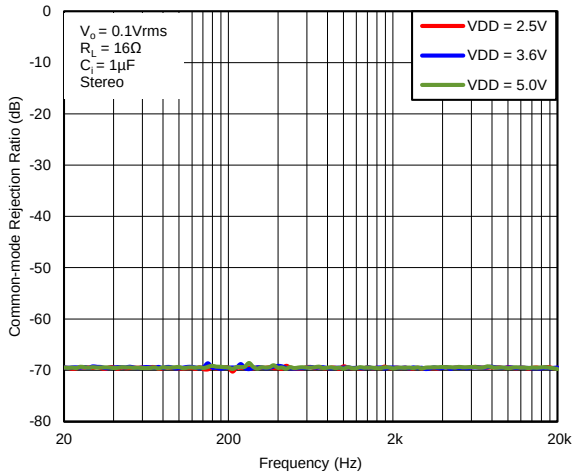

Figure 15. Common Mode Rejection Ratio vs Frequency

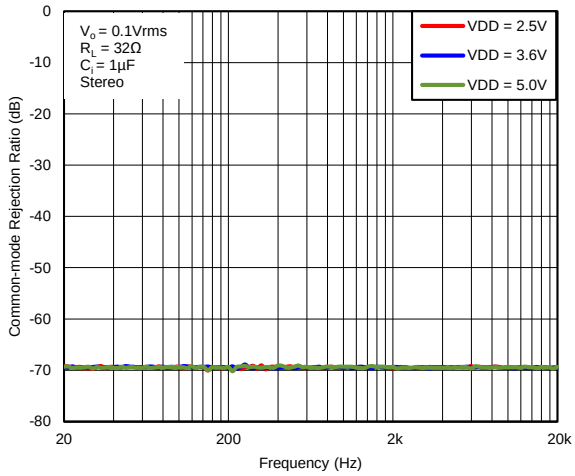

Figure 16. Common Mode Rejection Ratio vs Frequency

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All THD + N graphs taken with outputs out of phase (unless otherwise noted).

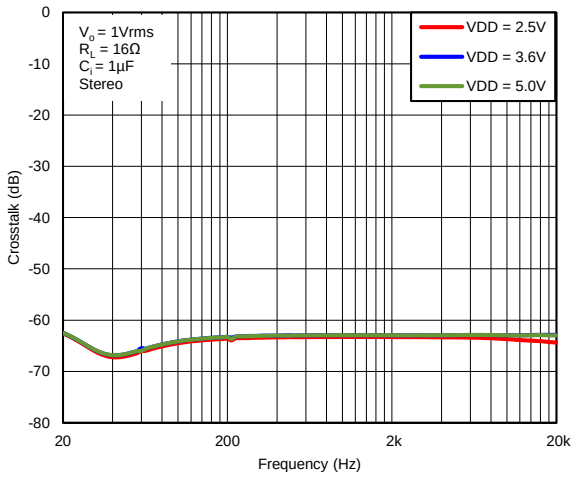

Figure 17. Crosstalk vs Frequency

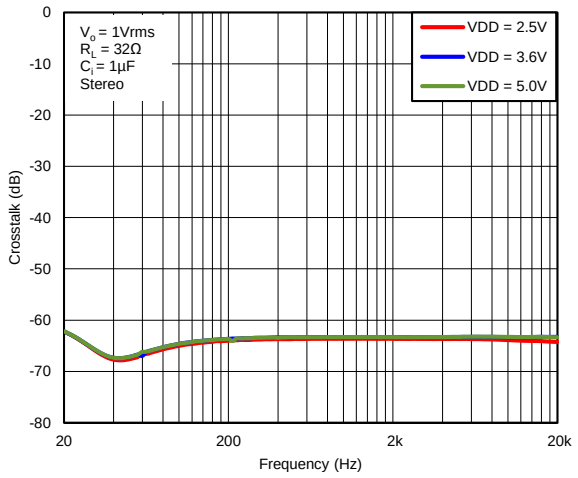

Figure 18. Crosstalk vs Frequency

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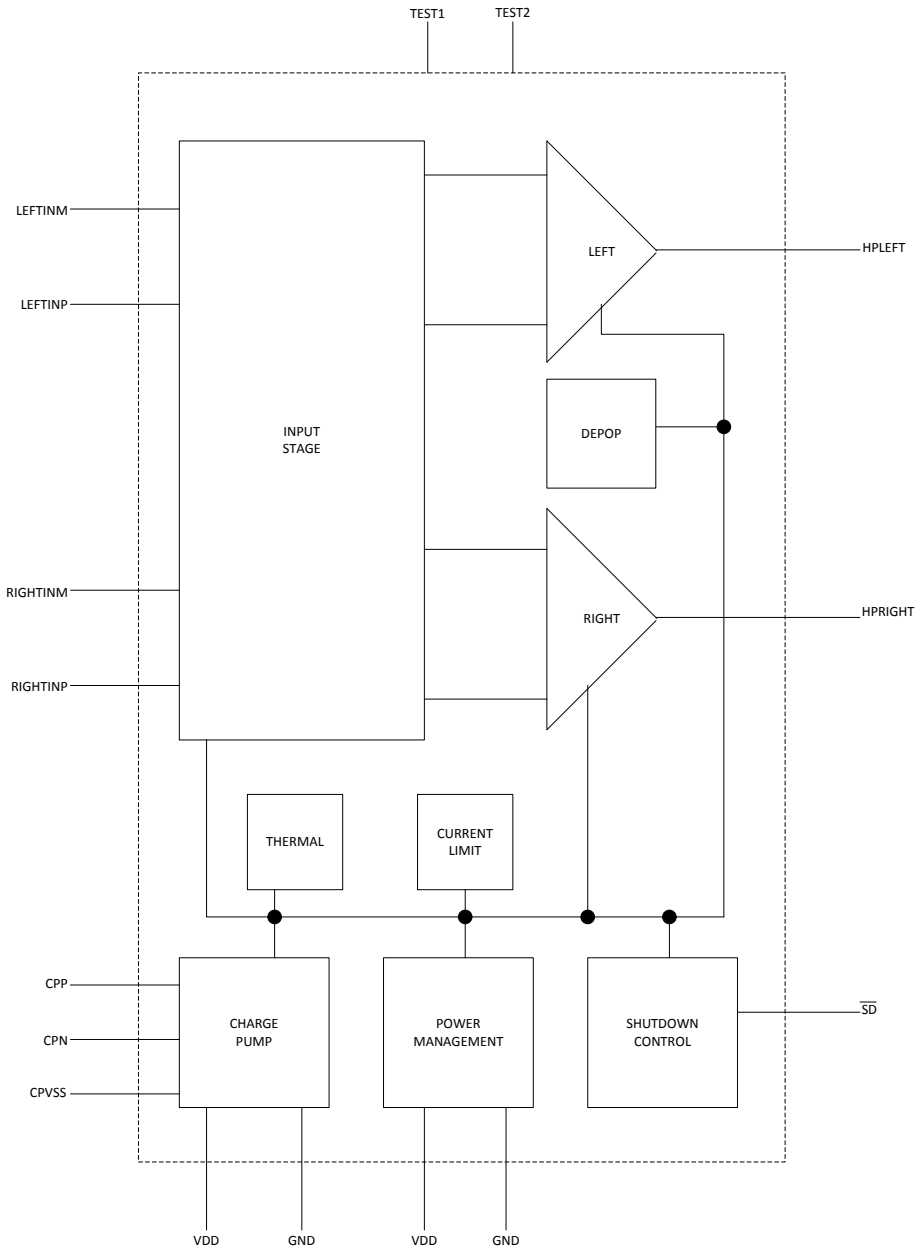
8 Detailed Description

8.1 Overview

Headphone channels and the charge pump are activated by asserting the $\overline{SD}$ pin to logic 1. The charge pump generates a negative supply voltage for the output amplifiers. This allows a 0 V bias at the outputs, eliminating the need for bulky output capacitors. The thermal block detects faults and shuts down the device before damage occurs. The current limit block prevents the output current from getting high enough to damage the device. The De-Pop block eliminates audible pops during power-up, power-down, and amplifier enable and disable events.

8.2 Functional Block Diagram



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8.3 Feature Description

8.3.1 Headphone Amplifiers

Single-supply headphone amplifiers typically require dc-blocking capacitors. The capacitors are required because most headphone amplifiers have a dc bias on the outputs pin. If the dc bias is not removed, power consumption will be higher, and large amounts of dc current rush through the headphones, potentially damaging them. The top drawing in Figure 19 illustrates the conventional headphone amplifier connection to the headphone jack and output signal.

DC blocking capacitors are often large in value. The headphone speakers (typical resistive values of 16 Ω or 32 Ω) combine with the dc blocking capacitors to form a high-pass filter. Equation 1 shows the relationship between the load impedance (R_L), the capacitor (C_O), and the cutoff frequency (f_C).

$$f_c = \frac{1}{2\pi R_L C_O} \tag{1}$$

C_O can be determined using Equation 2, where the load impedance and the cutoff frequency are known.

$$C_O = \frac{1}{2\pi R_L f_c} \tag{2}$$

If f_c is low, the capacitor must then have a large value because the load resistance is small. Large capacitance values require large package sizes. Large package sizes consume PCB area, stand high above the PCB, increase cost of assembly, and can reduce the fidelity of the audio output signal.

Two different headphone amplifier applications are available that allow for the removal of the output dc blocking capacitors. The capless amplifier architecture is implemented in the same manner as the conventional amplifier with the exception of the headphone jack shield pin. This amplifier provides a reference voltage, which is connected to the headphone jack shield pin. This is the voltage on which the audio output signals are centered. This voltage reference is half of the amplifier power supply to allow symmetrical swing of the output voltages. Do not connect the shield to any GND reference or large currents will result. The scenario can happen if, for example, an accessory other than a floating GND headphone is plugged into the headphone connector. See the second block diagram and waveform in Figure 19.

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Feature Description (continued)

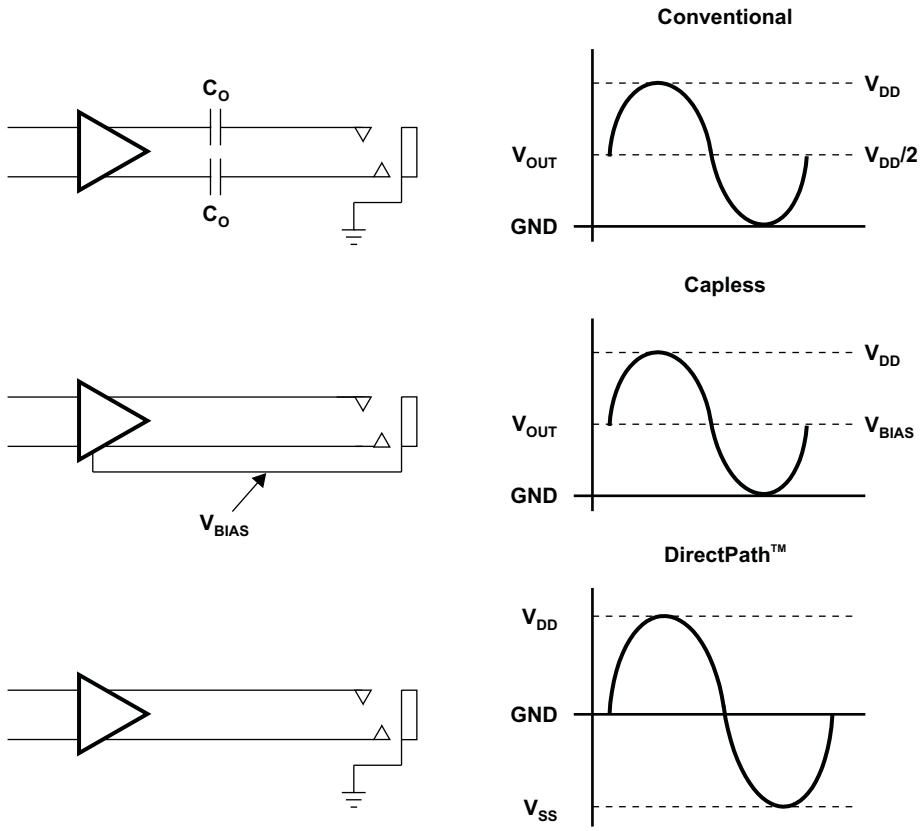

Figure 19. Amplifier Applications

The DirectPath™ amplifier architecture operates from a single supply but makes use of an internal charge pump to provide a negative voltage rail. Combining the user provided positive rail and the negative rail generated by the IC, the device operates in what is effectively a split supply mode. The output voltages are now centered at zero volts with the capability to swing to the positive rail or negative rail. The DirectPath™ amplifier requires no output dc blocking capacitors, and does not place any voltage on the sleeve. The bottom block diagram and waveform of Figure 19 illustrate the ground-referenced headphone architecture. This is the architecture of the TPA6133A2.

8.4 Device Functional Modes

8.4.1 Modes of Operation

The TPA6133A2 supports two modes of operation. When the $\overline{SD}$ pin is driven to logic 0, the device is in low power mode where the charge pump is powered down, the headphone channel is disabled and the outputs are pulled to ground. When the $\overline{SD}$ pin is driven to logic 1, the device enters an active mode with charge pump powered up and headphone channel enabled with channel gain of +4dB. The transition from inactive to active and active to inactive states is done softly to avoid audible artifacts.

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9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TPA6133A2 is a stereo DirectPath™ headphone amplifier with GPIO control. The TPA6133A2 has minimal quiescent current consumption, with a typical I_{DD} of 4.2 mA, making it optimal for portable applications.

9.2 Typical Application

Figure 20 shows a typical application circuit for the TPA6133A2 with a stereo headphone jack and supporting power supply decupling capacitors.

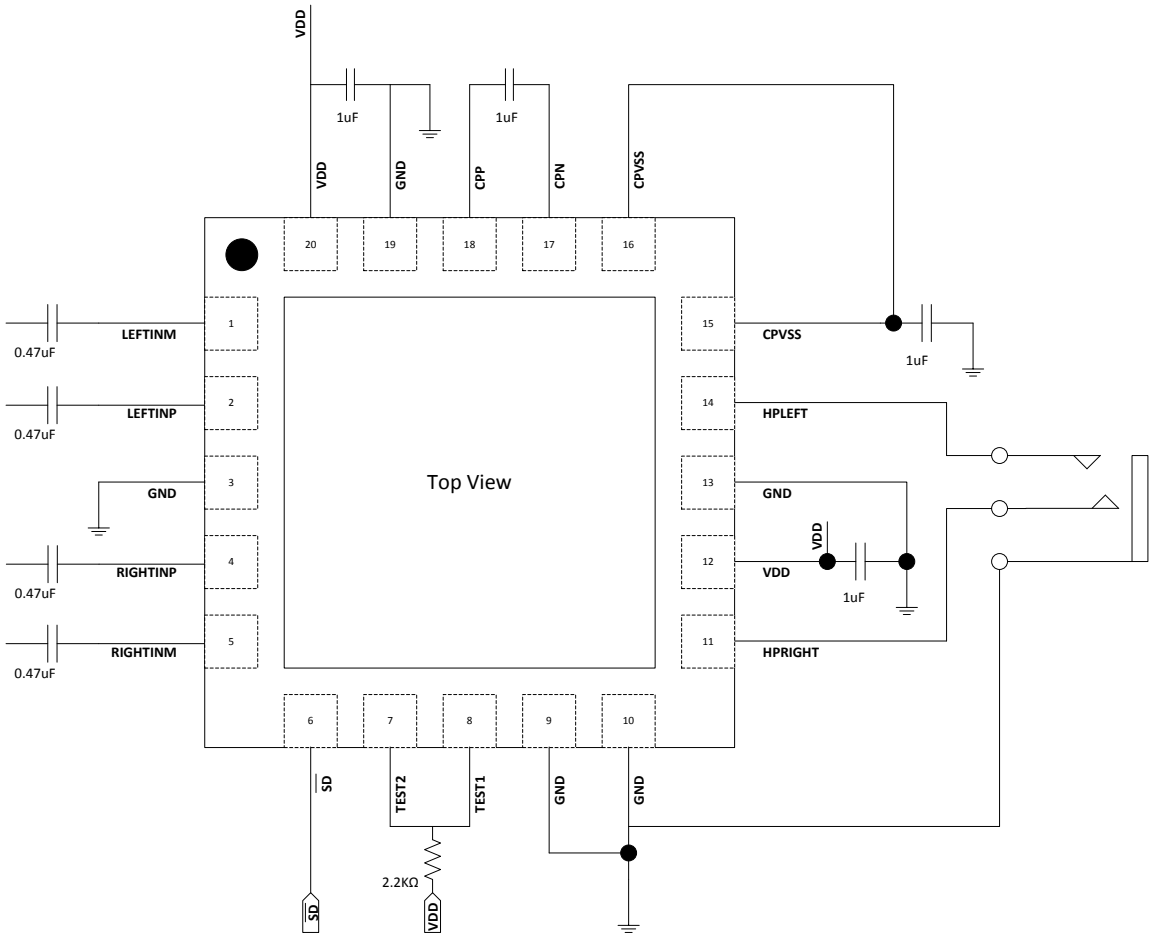

Figure 20. Simplified Applications Circuit

Typical Application (continued)

9.2.1 Design Requirements

For this design example, use the following as the input parameters.

Table 2. Design Parameters

DESIGN PARAMTER	EXAMPLE VALUE
Input voltage	2.5 V – 5.5 V
Minimum current limit	4 mA
Maximum current limit	6 mA

9.2.2 Detailed Design Procedure

9.2.2.1 Input-Blocking Capacitors

DC input-blocking capacitors block the dc portion of the audio source, and allow the inputs to properly bias. Maximum performance is achieved when the inputs of the TPA6133A2 are properly biased. Performance issues such as pop are optimized with proper input capacitors.

The dc input-blocking capacitors may be removed provided the inputs are connected differentially and within the input common mode range of the amplifier, the audio signal does not exceed ±3 V, and pop performance is sufficient.

C_{IN} is a theoretical capacitor used for mathematical calculations only. Its value is the series combination of the dc input-blocking capacitors, $C_{(DCINPUT\text{-}BLOCKING)}$. Use Equation 3 to determine the value of $C_{(DCINPUT\text{-}BLOCKING)}$. For example, if C_{IN} is equal to 0.22 µF, then $C_{(DCINPUT\text{-}BLOCKING)}$ is equal to about 0.47 µF.

$$C_{IN} = \frac{1}{2} C_{(DCINPUT\text{-}BLOCKING)} \tag{3}$$

The two $C_{(DCINPUT\text{-}BLOCKING)}$ capacitors form a high-pass filter with the input impedance of the TPA6133A2. Use Equation 3 to calculate C_{IN}, then calculate the cutoff frequency using C_{IN} and the differential input impedance of the TPA6133A2, R_{IN}, using Equation 4. Note that the differential input impedance changes with gain. The frequency and/or capacitance can be determined when one of the two values are given.

$$fc_{IN} = \frac{1}{2\pi R_{IN} C_{IN}} \quad \text{or} \quad C_{IN} = \frac{1}{2\pi fc_{IN} R_{IN}} \tag{4}$$

If a high pass filter with a -3 dB point of no more than 20 Hz is desired over all gain settings, the minimum impedance would be used in the above equation. The capacitor value by the above equation would be 0.215 µF. However, this is C_{IN}, and the desired value is for $C_{(DCINPUT\text{-}BLOCKING)}$. Multiplying C_{IN} by 2 yields 0.43 µF, which is close to the standard capacitor value of 0.47 µF. Place 0.47 µF capacitors at each input terminal of the TPA6133A2 to complete the filter.

9.2.2.2 Charge Pump Flying Capacitor and CPVSS Capacitor

The charge pump flying capacitor serves to transfer charge during the generation of the negative supply voltage. The CP_{VSS} capacitor must be at least equal to the flying capacitor in order to allow maximum charge transfer. Low ESR capacitors are an ideal selection, and a value of 1 µF is typical.

9.2.2.3 Decoupling Capacitors

The TPA6133A2 is a DirectPath™ headphone amplifier that requires adequate power supply decoupling to ensure that the noise and total harmonic distortion (THD) are low. Use good low equivalent-series-resistance (ESR) ceramic capacitors, typically 1.0 µF. Find the smallest package possible, and place as close as possible to the device V_{DD} lead. Placing the decoupling capacitors close to the TPA6133A2 is important for the performance of the amplifier. Use a 10 µF or greater capacitor near the TPA6133A2 to filter lower frequency noise signals. The high PSRR of the TPA6133A2 will make the 10 µF capacitor unnecessary in most applications.

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9.2.2.4 Optional Test Setup

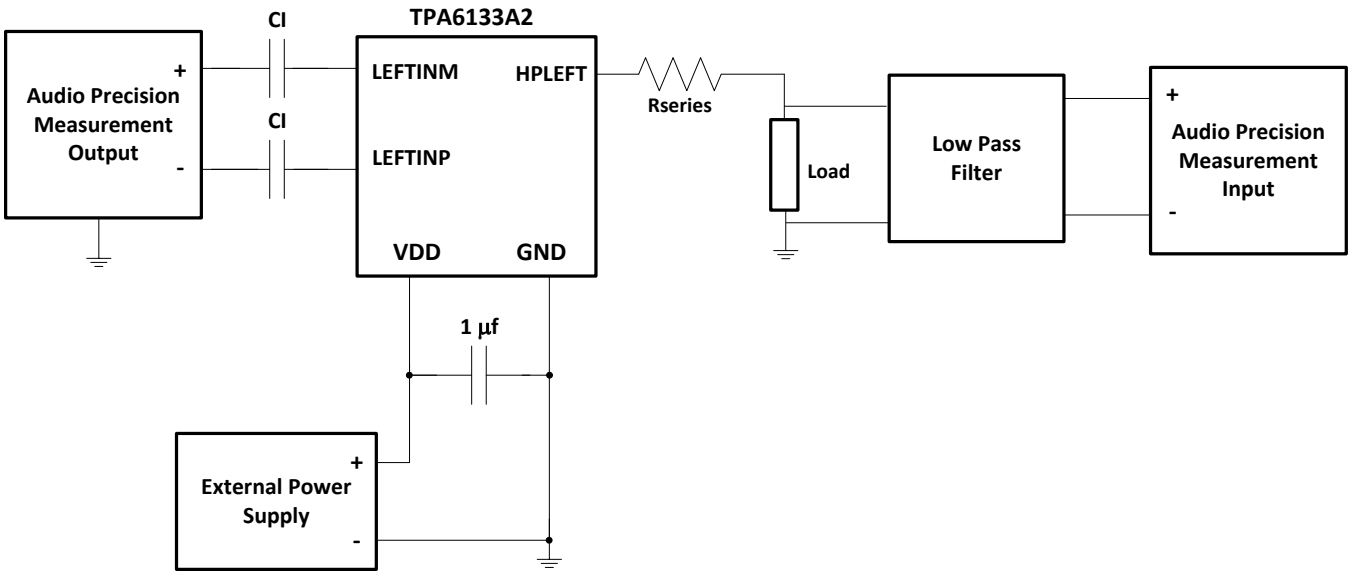

Figure 21. Test Setup

NOTE

Separate power supply decoupling caps are used on all VDD and CPVSS Pins

The low pass filter is used to remove harmonic content above the audible range.

9.2.3 Application Curves

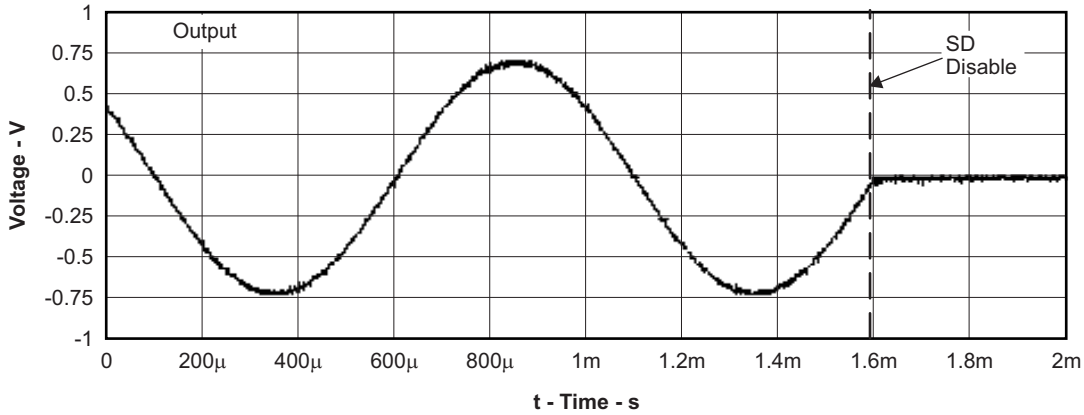

Figure 22. Shutdown Time

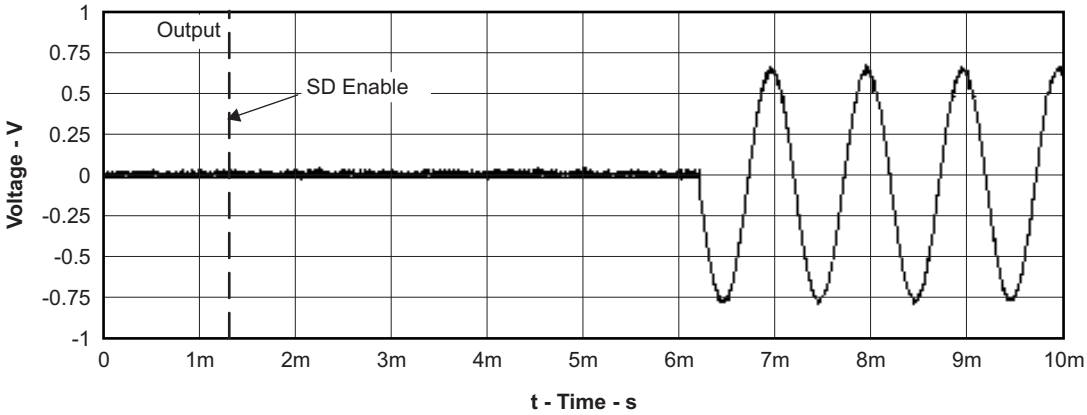

Figure 23. Startup Time

10 Power Supply Recommendations

The device is designed to operate from an input voltage supply range of 2.5 V to 5.5 V. Therefore, the output voltage range of power supply should be within this range and well regulated. The current capability of upper power should not exceed the max current limit of the power switch.

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11 Layout

11.1 Layout Guidelimes

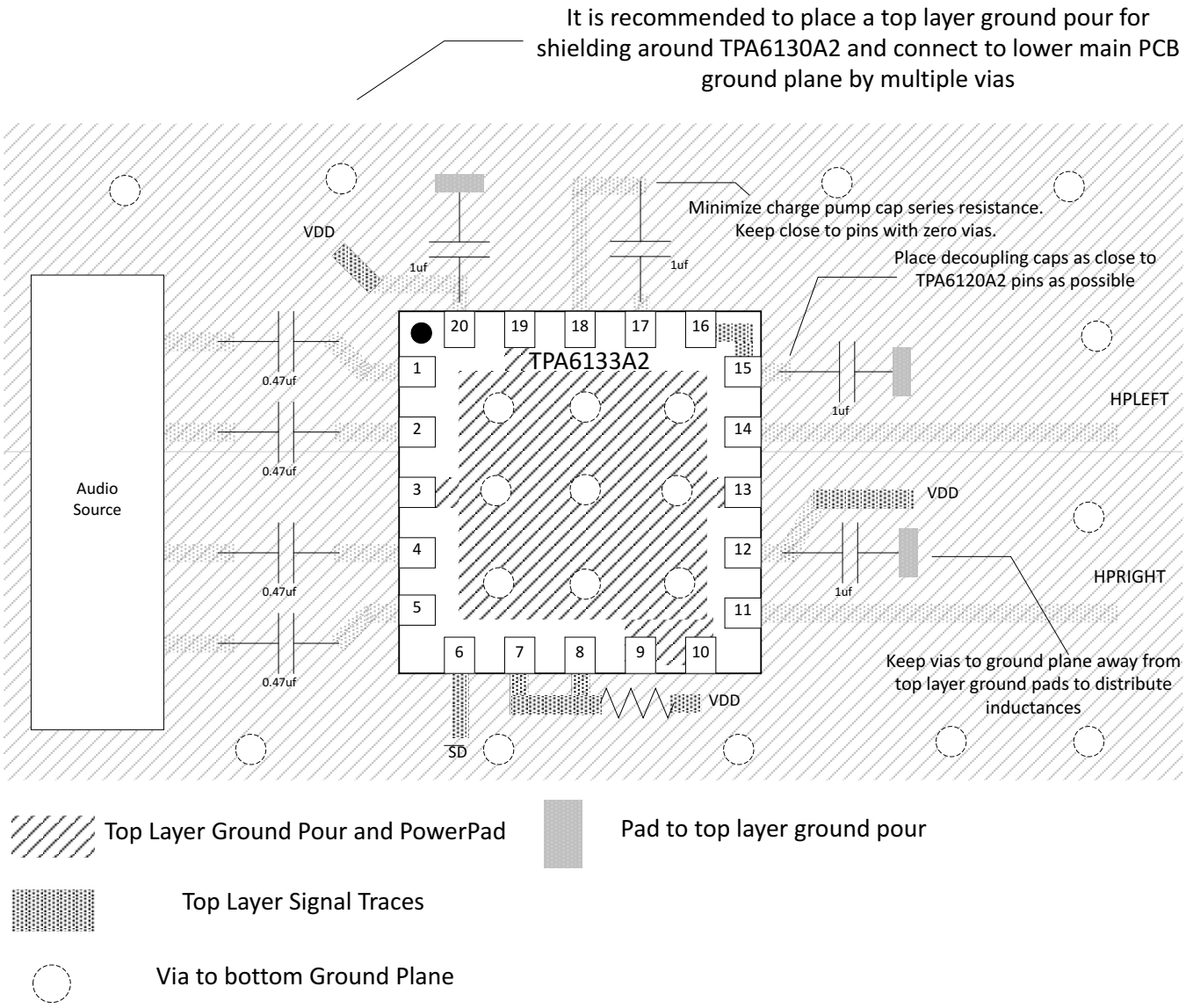
11.1.1 Exposed Pad On TPA6133A2RTJ Package

- Solder the exposed metal pad on the TPA6133A2RTJ QFN package to the a pad on the PCB. *The pad on the PCB may be grounded or may be allowed to float (not be connected to ground or power).*
- If the pad is grounded, it must be connected to the same ground as the GND pins (3, 9, 10, 13, and 19). See the layout and mechanical drawings at the end of the datasheet for proper sizing.
- Soldering the thermal pad improves mechanical reliability, improves grounding of the device, and enhances thermal conductivity of the package.

11.1.2 GND Connections

- The GND pin for charge pump should be decoupled to the charge pump V_{DD} pin, and the GND pin adjacent to the Analog V_{DD} pin should be separately decoupled to each other.

11.2 Layout Example



12 器件和文档支持

12.1 商标

DirectPath is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.2 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.3 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、首字母缩略词和定义。

13 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPA6133A2RTJR	Active	Production	QFN (RTJ) | 20	3000 | LARGE T&R	-	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	SIZ
TPA6133A2RTJR.A	Active	Production	QFN (RTJ) | 20	3000 | LARGE T&R	-	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	SIZ
TPA6133A2RTJR.B	Active	Production	QFN (RTJ) | 20	3000 | LARGE T&R	-	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	SIZ
TPA6133A2RTJT	Active	Production	QFN (RTJ) | 20	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	SIZ
TPA6133A2RTJT.B	Active	Production	QFN (RTJ) | 20	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	SIZ

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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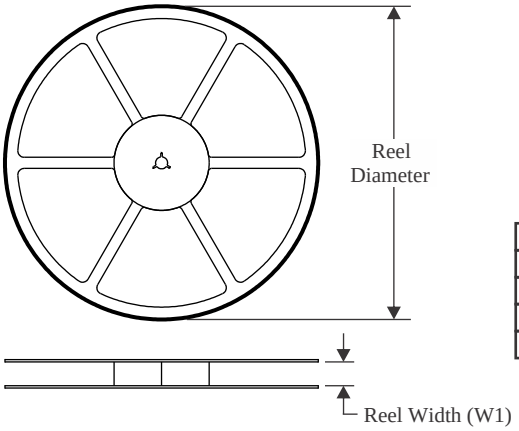
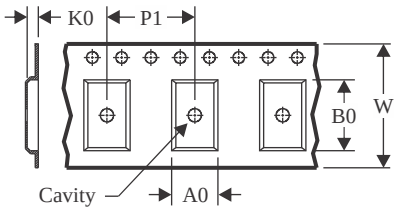
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

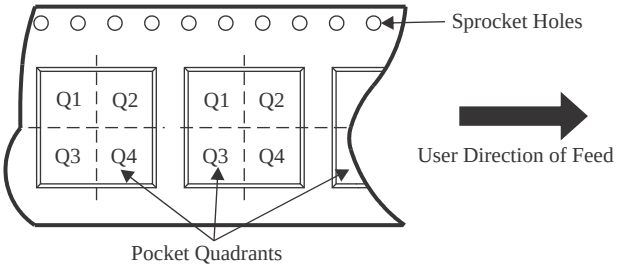


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

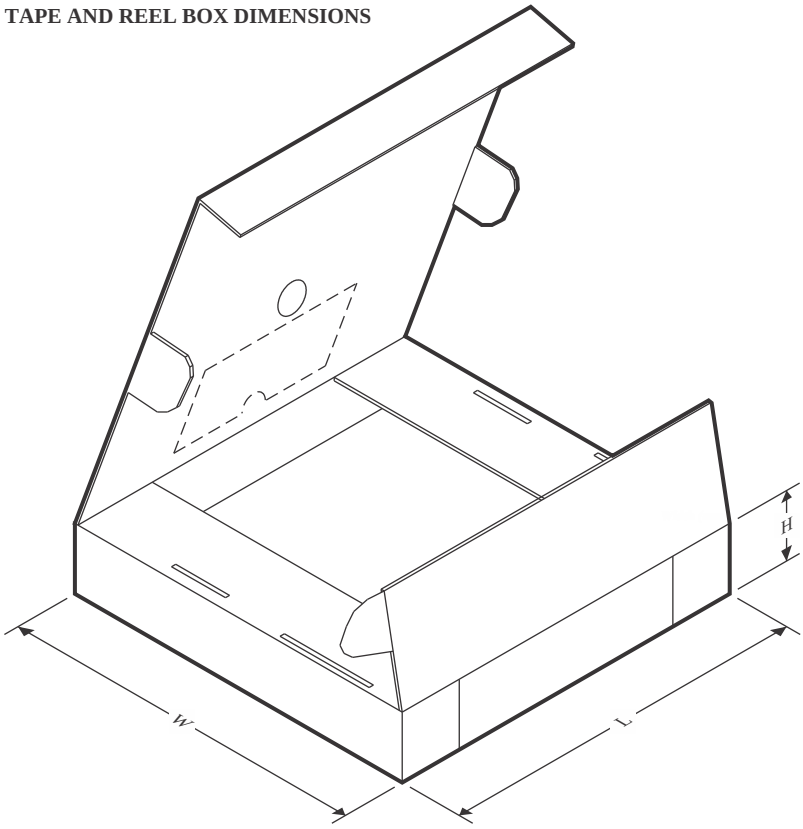
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPA6133A2RTJR	QFN	RTJ	20	3000	330.0	12.4	4.35	4.35	1.1	8.0	12.0	Q2
TPA6133A2RTJR	QFN	RTJ	20	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
TPA6133A2RTJR	QFN	RTJ	20	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
TPA6133A2RTJT	QFN	RTJ	20	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPA6133A2RTJR	QFN	RTJ	20	3000	338.0	355.0	35.0
TPA6133A2RTJR	QFN	RTJ	20	3000	360.0	360.0	36.0
TPA6133A2RTJR	QFN	RTJ	20	3000	346.0	346.0	33.0
TPA6133A2RTJT	QFN	RTJ	20	250	210.0	185.0	35.0

GENERIC PACKAGE VIEW

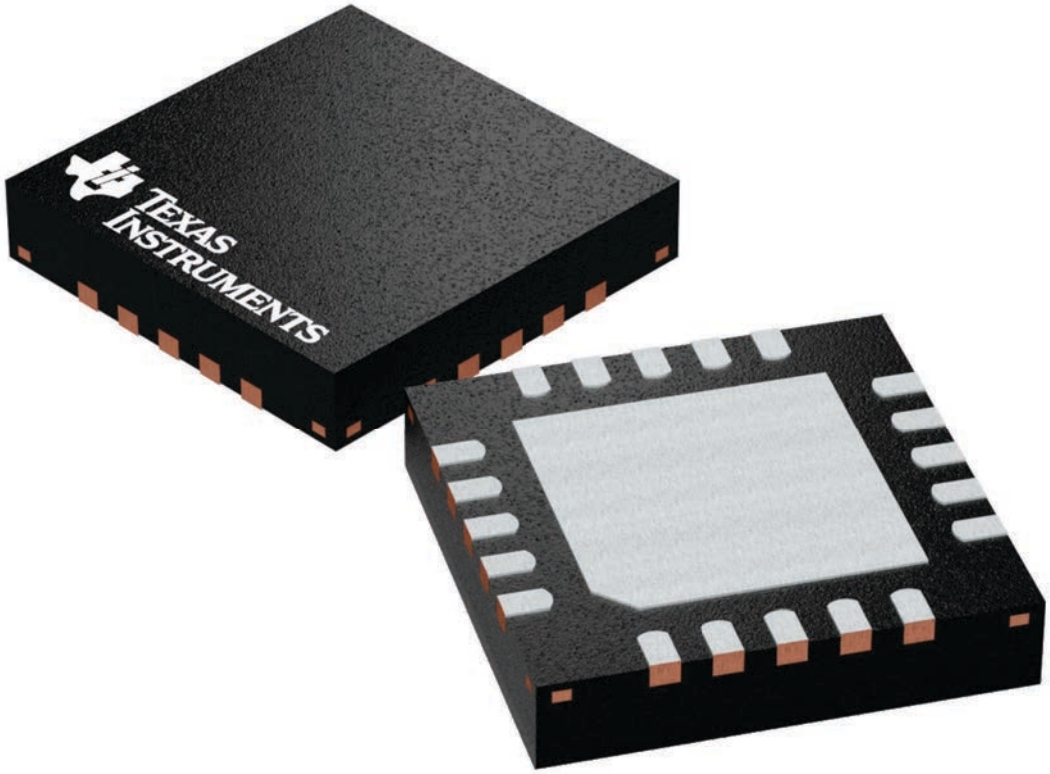
RTJ 20

WQFN - 0.8 mm max height

4 x 4, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

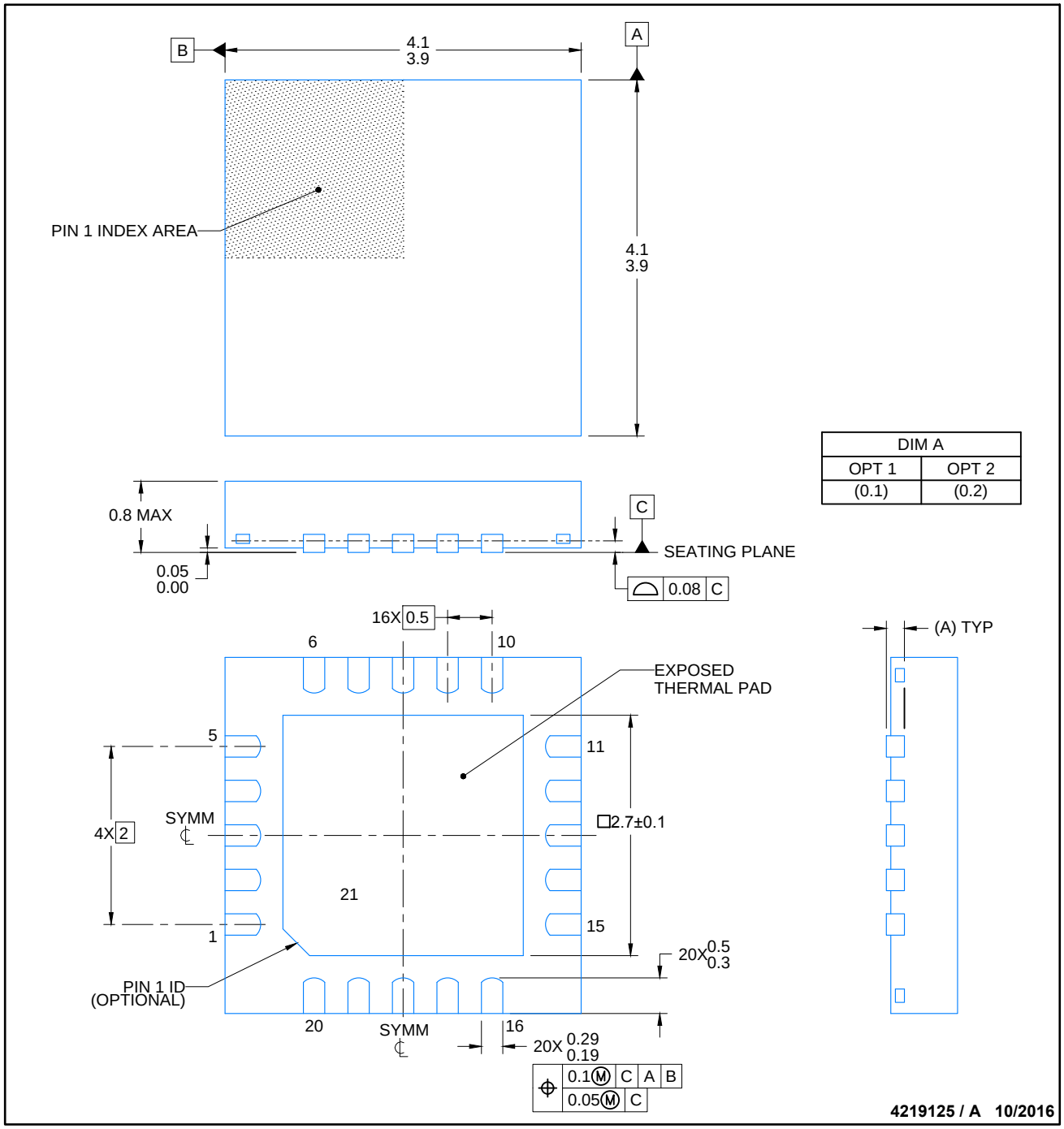


4224842/A

DATA BOOK
PACKAGE OUTLINE

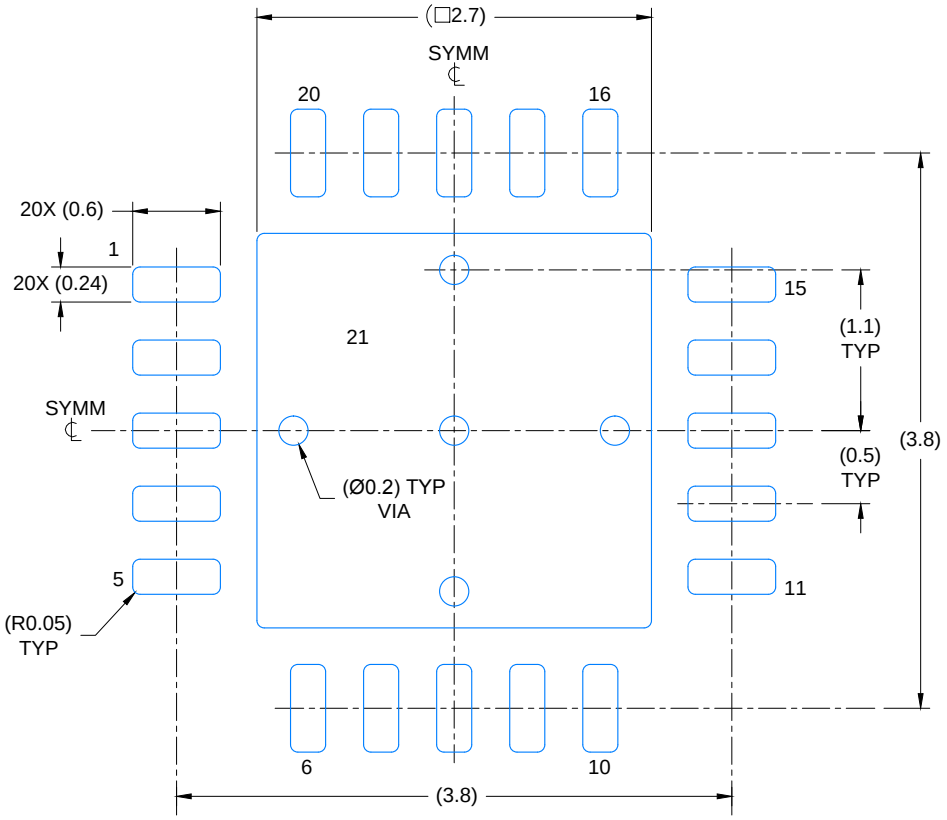
LEADFRAME EXAMPLE
4222370

DRAFTSMAN: H. DENG	DATE: 09/12/2016		DIMENSIONS IN MILLIMETERS
DESIGNER: H. DENG	DATE: 09/12/2016	TEXAS INSTRUMENTS SEMICONDUCTOR OPERATIONS	CODE IDENTITY NUMBER 01295
CHECKER: V. PAKU & T. LEQUANG	DATE: 09/12/2016		
ENGINEER: T. TANG	DATE: 09/12/2016	ePOD, RTJ0020D / WQFN, 20 PIN, 0.5 MM PITCH	
APPROVED: E. REY & D. CHIN	DATE: 10/06/2016		
RELEASED: WDM	DATE: 10/24/2016		
TEMPLATE INFO: EDGE# 4218519	DATE: 04/07/2016	SCALE 15X / SIZE A / 4219125	REV A / PAGE 1 OF 5



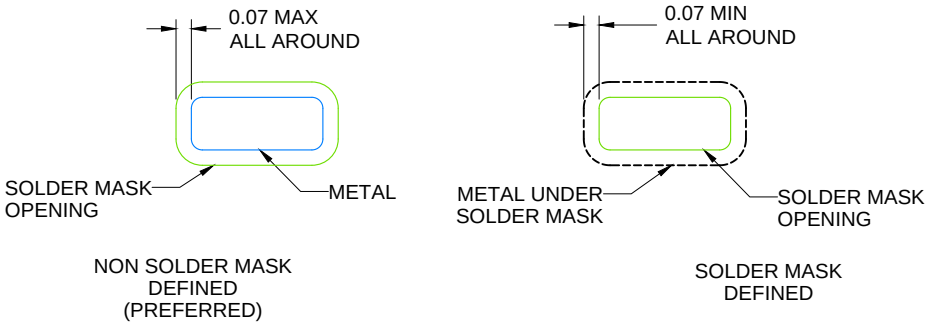
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE

SCALE: 20X

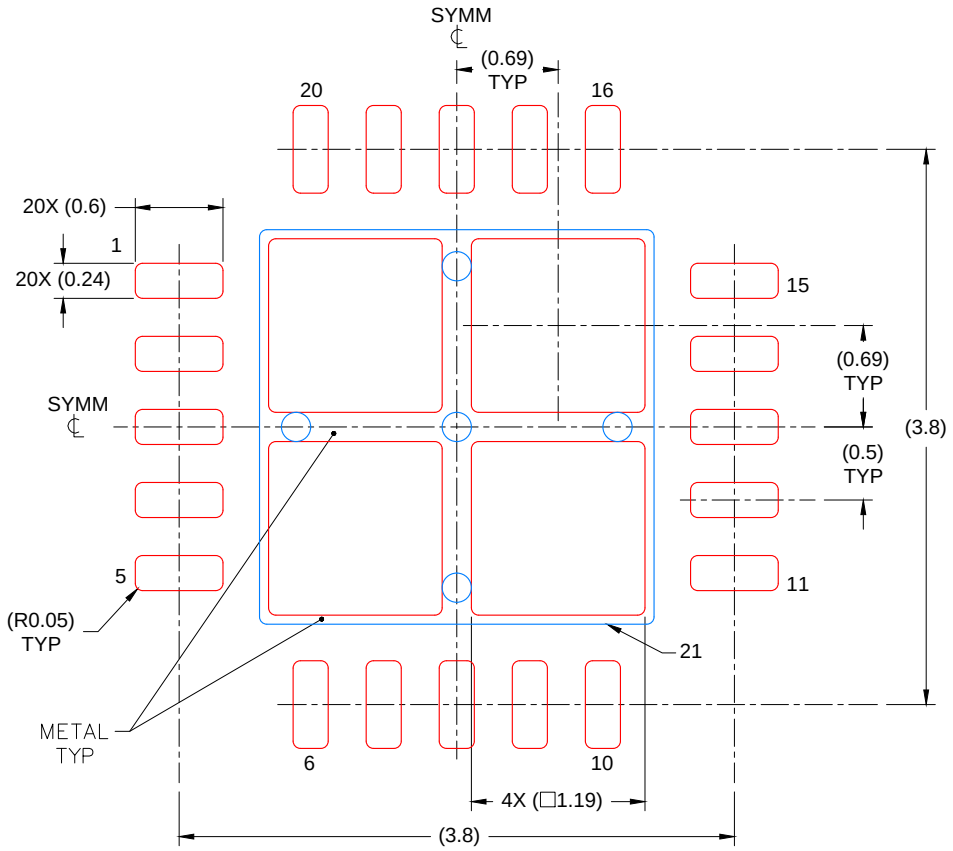


SOLDER MASK DETAILS

4219125 / A 10/2016

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
78% PRINTED COVERAGE BY AREA
SCALE: 20X

4219125 / A 10/2016

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations..

REVISIONS

REV	DESCRIPTION	ECR	DATE	ENGINEER / DRAFTSMAN
A	RELEASE NEW DRAWING	2160736	10/24/2016	T. TANG / H. DENG

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最后更新日期：2025 年 10 月